

## Electronic Acknowledgement Receipt

<b>EFS ID:</b>	8349805
<b>Application Number:</b>	10565621
<b>International Application Number:</b>	
<b>Confirmation Number:</b>	2319
<b>Title of Invention:</b>	Stacked structure and production method thereof
<b>First Named Inventor/Applicant Name:</b>	Hubert Moriceau
<b>Customer Number:</b>	90678
<b>Filer:</b>	Jasper W. Dockrey
<b>Filer Authorized By:</b>	
<b>Attorney Docket Number:</b>	9905-37 (BIF116044/US)
<b>Receipt Date:</b>	03-SEP-2010
<b>Filing Date:</b>	25-JUL-2006
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<b>Application Type:</b>	U.S. National Stage under 35 USC 371

### Payment information:

Submitted with Payment	no
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### File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	Demeester_et_al_Epitaxial_Lift-Off_and_Its_Appls.pdf	1057147 e514a67e257a78c59c8f8a60d19a80596c46b7c	no	13

**Warnings:**

**Information:**

2	NPL Documents	Denteneer_et_al_Hydrogen_Diffusion_and_Passivation_of_Silicon_Hollow_Impurities.pdf	299205 9a4bc761628b459b1079103d24c1956759a6b8ba	no	5
<b>Warnings:</b>					
<b>Information:</b>					
3	NPL Documents	Denteneer_et_al_Structure_and_Properties_of_Hydrogen-Impurity_Pairs.pdf	342276 a91f56eef0706a0e784c4a52627a5ce12a8a	no	4
<b>Warnings:</b>					
<b>Information:</b>					
4	NPL Documents	DiCioccio_et_al_Silicon_Carbide_on_Insulator_Formation.pdf	130526 11f5c4678f1bb857e65d732574c99b298302a4	no	2
<b>Warnings:</b>					
<b>Information:</b>					
5	NPL Documents	Dirks_AG_et_al_Columnar_Microstructure_in_Vapor_Deposited_Thin_Films.pdf	1187199 6b09b5562b3c2be538f3a3781ca71cc23e78fc3	no	15
<b>Warnings:</b>					
<b>Information:</b>					
6	NPL Documents	Duo_et_al_Comparison_Between_The_Different.pdf	821079 6519e426a9baed33c945405b5176daab5eae0d	no	6
<b>Warnings:</b>					
<b>Information:</b>					
7	NPL Documents	Duo-et-al-Evolution-of-Hydrogen-and-Helium_1.PDF	549396 0e37d771d8074bc5d48a1070836ae0637281a	no	6
<b>Warnings:</b>					
<b>Information:</b>					
8	NPL Documents	Eaglesham_White_et_al_Equilibrium_Shape_of_Si.pdf	272298 56022ce8916cd728132545786af7de7e3d2897b	no	4
<b>Warnings:</b>					
<b>Information:</b>					
9	NPL Documents	EerNisse_E-Compaction_of_Ion-Implanted_Fused_Silica.pdf	768866 8a4542aa7694711b3130530536c40297c151017f1c2	no	8
<b>Warnings:</b>					
<b>Information:</b>					
10	NPL Documents	EerNisse_EP-Role_of_Integrated_Lateral_Stress_In_Surface_Deformation_of_He_Implanted_Surfaces.pdf	801341 c1cd258efac75d0111b6a2253d5f97c61a70	no	9
<b>Warnings:</b>					
<b>Information:</b>					

11	NPL Documents	Evans_JH_An_Interbubble_Fracture_Mechanism_Of_Blisters.pdf	869679 ds0c3661db7161668c795ee119344efcd0789bb	no	12
<b>Warnings:</b>					
<b>Information:</b>					
12	NPL Documents	Feijoo_et_al-Prestressing_of_Bonded.pdf	390788 6e1548bd0647157ac8b32ed111218db8be184d3	no	9
<b>Warnings:</b>					
<b>Information:</b>					
13	NPL Documents	Feng_et_al_Generalized_Formula_For_Curvature.pdf	137308 7d09bc779761717Aee52a46a8a7b1b451b290e415	no	3
<b>Warnings:</b>					
<b>Information:</b>					
14	NPL Documents	Garner_DM-The_Fabrication_Of_A_Partial_SOI_Substrate.pdf	376649 3ab246c0d9647a9129003fda1800db2635f4d24	no	6
<b>Warnings:</b>					
<b>Information:</b>					
15	NPL Documents	Gerasimenko_N-Infrared_Absorption_of_Silicon_Irradiated_by_Phtrons.pdf	423407 4ba07b0abed17bbce9dc0753daab01e127c32edc2	no	7
<b>Warnings:</b>					
<b>Information:</b>					
16	NPL Documents	Ghandi_Sorab-VSLI_Fabrication_Principles-Silicon_and_Gallium_Arsenide.pdf	145184 d4b5200b786a70a5146edc11fa09801416e7917	no	4
<b>Warnings:</b>					
<b>Information:</b>					
17	NPL Documents	Greenwald_AC-Pulsed-Electron-Beam_Annealing_of_Ion-Implantation_Damage.pdf	364299 78f4ac2ee753b237360566303131285a2a16d0aa	no	4
<b>Warnings:</b>					
<b>Information:</b>					
18	NPL Documents	Grovenor_C_Microelectronic_Materials.pdf	183072 d46db7b-6d2952578bf1c50492e143c3079f2099	no	5
<b>Warnings:</b>					
<b>Information:</b>					
19	NPL Documents	Guilhalmenc_C_et_al_Characterization_By_Atomic_Force_Microscopy_of_the_SOI_Layer.pdf	266316 d68f8a80f1ba61d4709052b74b3b18ab7da5ed61	no	4
<b>Warnings:</b>					
<b>Information:</b>					

20	NPL Documents	Haisma_et_al_Silicon_on_Insulator-Wafer_Bonding.pdf	1279237 3c394f5ab49822c6d4d465963b55fac13c8bade7	no	18
<b>Warnings:</b>					
<b>Information:</b>					
21	NPL Documents	Hamaguchi_et_al_Device_Layer_Transfer_Technique.pdf	157984 e2d817472a0db1c245cdd84154ac78a095c5a1ba	no	3
<b>Warnings:</b>					
<b>Information:</b>					
22	NPL Documents	Hamaguchi_et_al_Novel_LSI-SOI_Wafer.pdf	308961 ba28f1f283488256918f579a21f30f51a105e8d8f	no	4
<b>Warnings:</b>					
<b>Information:</b>					
23	NPL Documents	Henttinen_et_al-Mechanically_Induced_Si_Layer.pdf	248942 084c50898bac7d3db49a6611752ad4c294e97bae1	no	3
<b>Warnings:</b>					
<b>Information:</b>					
24	NPL Documents	Hulett_DM_et_al_Ion_Nitriding_and_Ion_Impantation.pdf	228302 8894673d4381b797acde884eb3589dc0d353a02	no	4
<b>Warnings:</b>					
<b>Information:</b>					
25	NPL Documents	IBM_Technical_Disclosure_Bulletin-Isolation_By_Inert_Ion_Implantation.pdf	31620 68441c8721ef5dacefa339e8b1ba65aceaf5176c	no	1
<b>Warnings:</b>					
<b>Information:</b>					
26	NPL Documents	IBM-Tech-Disclosure-SOI-Interposer.PDF	135377 a8bc73684624620682a79ed1738c3762d64d8a1	no	5
<b>Warnings:</b>					
<b>Information:</b>					
27	NPL Documents	Jap-OA-Dated-10-25-07-2002-581572.pdf	209378 a158ec563d26ac19a62f40664cd2665eac7a895	no	5
<b>Warnings:</b>					
<b>Information:</b>					
28	NPL Documents	Jaussaud_C_et_al-Microstructure_of_Silicon_Implanted_With_High_Dose_Oxygen_Ions.pdf	393224 8ac7aedd616d798f34e63380534854f5e0ee11	no	3
<b>Warnings:</b>					
<b>Information:</b>					

29	NPL Documents	Johnson-High_Fluence_Deuteron_Bombardment_of_Silicon.pdf	837642 461886ca21720fde38f9adfd40226161ef47f	no	9
<b>Warnings:</b>					
<b>Information:</b>					
30	NPL Documents	Jones_KS_et_al-A_Systematic_Analysis_of_Defects_in_Ion_Implanted_Silicon.pdf	2789593 cd8c4ef18b7c5a8b8ca5c95a81c4d4456bde1a3b3	no	35
<b>Warnings:</b>					
<b>Information:</b>					
31	NPL Documents	Jones_et_al_Enhanced_elimination_of_implantation_damage_upon_exceeding_the_solid_solubility.pdf	379786 d146c99b484857c996c6ba8c-a028f3875cd7a5	no	4
<b>Warnings:</b>					
<b>Information:</b>					
32	NPL Documents	Kamada_et_al-Observation_of_Blistering_and_Amorphization_on_Germanium_Surface_After_keV.pdf	519461 b8f8ec8bf5e10bde84030b7bc6ec361118d1ef	no	6
<b>Warnings:</b>					
<b>Information:</b>					
33	NPL Documents	Klem_Characteristics_of_Lift.pdf	393669 58ac598a9981860788a6bf8aaefc1b294377c930	no	6
<b>Warnings:</b>					
<b>Information:</b>					
34	NPL Documents	Komarov_et_al-Crystallographic_Nature_and_Formation_Mechanisms_of_Highly_Irregular_Structure.pdf	687131 9b8bc8d89eeccdc5e8118ab92d798cda91581fe	no	9
<b>Warnings:</b>					
<b>Information:</b>					
35	NPL Documents	Kucheyev_et_al-Ion_Implantation_Into_GaN.pdf	3044381 cd15f5ca166825437c8b8cd849641260f98073	no	58
<b>Warnings:</b>					
<b>Information:</b>					
36	NPL Documents	Laporte-A-et-al-Charged-Defects-at-the-Interface.pdf	1355175 4674168908c4ba348b995a89abdf8bbab59a85e	no	5
<b>Warnings:</b>					
<b>Information:</b>					
37	NPL Documents	Li_J_Novel_Semiconductor_Substrate_Formed_By.pdf	51901 9a3ee8030c4aac5f68ba8ab152330153ec42508	no	2
<b>Warnings:</b>					
<b>Information:</b>					

38	NPL Documents	Ligeon_E-Hydrogen_Implantation_in_Silicon_Between_1-5_and_60_KeV.pdf	820674 2f6c18c1a27c581cd47282bd13459a2c0b1	no	9
<b>Warnings:</b>					
<b>Information:</b>					
39	NPL Documents	Liu_et_al-Ion_Implantation_in_GaN_at_Liquid-Nitrogen_Temperature.pdf	461874 e98f35f0bdc00202115af556f9b505c17cc34800	no	6
<b>Warnings:</b>					
<b>Information:</b>					
40	NPL Documents	Lu_X-SOI-Material-Technology-Using-Plasma_1.PDF	239638 104711bc0d5d4dfe1931572539a057db0b96547	no	2
<b>Warnings:</b>					
<b>Information:</b>					
41	NPL Documents	Maleville-et-al-Physical-Phenomena-Involved_1.PDF	843600 4e0d465c12447e064fc91917c0d4916d90c294	no	18
<b>Warnings:</b>					
<b>Information:</b>					
42	NPL Documents	Maleville_C_Wafer_Bonding_and_High-Implantation.pdf	266110 47c85a90b27c0a7ab73c57423c63ba03ba3	no	6
<b>Warnings:</b>					
<b>Information:</b>					
43	NPL Documents	Manuaba_A-Comparative_Study_on_Fe-Ni_Cri_P_Metallic_Glass_and_Its_Polycrystalline_Modification.pdf	1160732 693a4c311b0a0850ed45975c840ac491a13b9a5	no	11
<b>Warnings:</b>					
<b>Information:</b>					
44	NPL Documents	Matsuda_et_al_Large_Diameter_Beam_Implantation_System.pdf	129012 6f7a95c5000c122800c5f6cc21b1e01b72f2a2	no	3
<b>Warnings:</b>					
<b>Information:</b>					
45	NPL Documents	Matsuo_et_al_Abnormal_solid_solution_and_activation_behavior_in_GA-implanted_Si100.pdf	207625 9945d8f1ba5f79dc9a0b97e0be4ac0f014a5007	no	3
<b>Warnings:</b>					
<b>Information:</b>					
46	NPL Documents	Mishima_Y_and_T_Yagishita_Investigation_Of_The_Bubble_Formation.pdf	165000 64b75f6f1210be7218464bb1994db1b268f618d2	no	3
<b>Warnings:</b>					
<b>Information:</b>					

47	NPL Documents	Miyagawa_S_et_al-Helium_Reemission_During_Impantation_of_Silicon_Carbide.pdf	375866 e0b09206a6f30473d3e2d0e7c587ed15108749	no	5
<b>Warnings:</b>					
<b>Information:</b>					
48	NPL Documents	Miyagawa_S_et_al-Surface_Structures_of_Silicon_Carbide_Irradiated_With_Helium_Ions.pdf	774178 c70a13420b4b76c0577f6b161867947e0d8	no	9
<b>Warnings:</b>					
<b>Information:</b>					
49	NPL Documents	Monemar_B-Shallow_Impurities_in_Semiconductors.pdf	485747 a0d11112c4d8b0227d8d8c1779c09952c05e97	no	6
<b>Warnings:</b>					
<b>Information:</b>					
50	NPL Documents	Moreau_Wayne_M_Semiconductor_Lithography_Principles.pdf	497940 90914d61451ef12c7c742510ac2569aeb2adcb	no	17
<b>Warnings:</b>					
<b>Information:</b>					
51	NPL Documents	Moriceau_H_et_al_A_New_Characterization_Process_Used_To.pdf	303042 0c5008f402bd4d8c35e74961e03b0c2d253700	no	6
<b>Warnings:</b>					
<b>Information:</b>					
52	NPL Documents	Moriceau_H_et_al_Cleaning_and_Polishing_As_Key_Steps.pdf	151493 0c3d0ed195b4e959235d83b25f5e4e7adeec96	no	2
<b>Warnings:</b>					
<b>Information:</b>					
53	NPL Documents	Moriceau_H_et_al_The_Smart_Cut_Process_As_A_Way_To.pdf	116346 ba18a36186c08338d5194ca20c2917c9bae871	no	2
<b>Warnings:</b>					
<b>Information:</b>					
54	NPL Documents	Moriceau_Vol99-1_Meeting_Abstract.pdf	156085 a01e0749dca863990bae0f22d08d175e07a0b	no	2
<b>Warnings:</b>					
<b>Information:</b>					
55	NPL Documents	Munteanu-et-al-Detailed-Characteristics-of-Unibond-Material.pdf	186594 0803f9c1acac5f98031d02c06134352340fa2a	no	4
<b>Warnings:</b>					
<b>Information:</b>					

56	NPL Documents	Myers_DR-The_Effects_of_Ion-Implantation_Damage_on_The_First_Order_Raman_Spectra.pdf	676976 5f802e6a3c3a0e9811528805a03bd7b7a31d07c	no	7
Warnings:					
Information:					
57	NPL Documents	Neethling_CE_et_al-Identification_of_Hydrogen_Platelets_in_Proton_Bombardment_GaAs.pdf	436026 b8cb35d1f54886cad519b51482af02e8077b0937	no	5
Warnings:					
Information:					
58	NPL Documents	Nichols_C_et_al-Properties_of_Hydrogen_in_Crystalline_Silicon.pdf	740397 f8eb72d09cAec2b7d57d8c180452ca0318c5bd78	no	4
Warnings:					
Information:					
59	NPL Documents	Nicoletti_S_et_al-Bi-Epitaxial_YBCO_Grain_Boundary_Josephson_Junctions.pdf	869860 06a47a30171ce37d689712b6d7925f8e672d26	no	13
Warnings:					
Information:					
Total Files Size (in bytes):			32502614		
This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.					
New Applications Under 35 U.S.C. 111					
If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.					
National Stage of an International Application under 35 U.S.C. 371					
If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.					
New International Application Filed with the USPTO as a Receiving Office					
If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.					